



Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _A = +25°C
	700mΩ @ V_{GS} = -4.5V	-460mA
-20V	900mΩ @ V _{GS} = -2.5V	-420mA
	1300mΩ @ V _{GS} = -1.8V	-350mA

Description and Applications

This MOSFET is designed to meet the stringent requirements of Automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

- DC-DC Converters
- Load Switch
- Power Management Functions

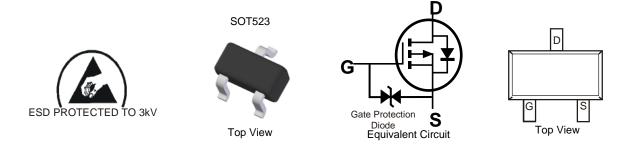
20V P-CHANNEL ENHANCEMENT MODE MOSFET

Features and Benefits

- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- ESD Protected Up To 3kV
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

Mechanical Data

- Case: SOT523
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Alloy 42 Leadframe. Solderable per MIL-STD-202, Method 208 (3)
- Terminal Connections: See Diagram
- Weight: 0.002 grams (Approximate)



Ordering Information (Note 5)

Part Number	Case	Packaging
DMG1013TQ-7	SOT523	3000/Tape & Reel

1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.

2. See http://www.diodes.com/quality/lead_free.htmlfor more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to http://www.diodes.com/product_compliance_definitions.html.

5. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information

PA1	ΥM

PA1 = Product Type Marking Code YM = Date Code Marking Y = Year (ex: D = 2016) M = Month (ex: 9 = September)

Date Code Key

Notes:

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Year	2016	20	17	2018	2019	20	20	2021	2022	20	23	2024
Code	D	E	=	F	G	ŀ	-	I	J		<	L
Month	Jan	Feb	Mar	Apr	Мау	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V _{DSS}	-20	V
Gate-Source Voltage		V _{GSS}	±6	V	
Drain Current (Note 6)	Steady State	T _A = +25°C T _A = +85°C	ID	-0.46 -0.33	A
Pulsed Drain Current (Note 7)		I _{DM}	-6	A	

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 6)	PD	0.27	W
Thermal Resistance, Junction to Ambient (Note 6)	$R_{ ext{ heta}JA}$	461	°C/W
Operating and Storage Temperature Range	T _{J,} T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						•
Drain-Source Breakdown Voltage	BV _{DSS}	-20	-	-	V	$V_{GS} = 0V, I_D = -250 \mu A$
Zero Gate Voltage Drain Current TJ = +25°C	I _{DSS}	-	-	-100	nA	$V_{DS} = -20V, V_{GS} = 0V$
Gate-Source Leakage	I _{GSS}	-	-	±2.0	μA	$V_{GS} = \pm 4.5 V, V_{DS} = 0 V$
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	V _{GS(TH)}	-0.5	-	-1.0	V	$V_{DS} = V_{GS}$, $I_D = -250 \mu A$
			0.5	0.7		$V_{GS} = -4.5V, I_D = -350mA$
Static Drain-Source On-Resistance	R _{DS(ON)}	-	0.7	0.9	Ω	$V_{GS} = -2.5V, I_D = -300mA$
			1.0	1.3		$V_{GS} = -1.8V, I_D = -150mA$
Forward Transfer Admittance	Y _{fs}	-	0.9	-	S	$V_{DS} = -10V, I_D = -250mA$
Diode Forward Voltage	V _{SD}		-0.8	-1.2	V	$V_{GS} = 0V, I_{S} = -150mA$
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	Ciss	-	59.76	-	pF	
Output Capacitance	Coss	-	12.07	-	pF	$V_{DS} = -16V, V_{GS} = 0V,$ - f = 1.0MHz
Reverse Transfer Capacitance	Crss	-	6.36	-	pF	1 = 1.00012
Total Gate Charge	Qg	-	580	-	рС	
Gate-Source Charge	Q _{gs}	-	104	-	рС	V _{GS} = -4.5V, V _{DS} = -10V, I _D = -250mA
Gate-Drain Charge	Q _{gd}	-	125	-	рС	ID = -250IIIA
Turn-On Delay Time	t _{D(ON)}	-	5.1	-	ns	
Turn-On Rise Time	t _R	-	8.1	-	ns	$V_{DD} = -10V, V_{GS} = -4.5V,$
Turn-Off Delay Time	t _{D(OFF)}	-	28.4	-	ns	$R_{\rm L} = 47\Omega, R_{\rm g} = 10\Omega,$
Turn-Off Fall Time	tF	-	20.7	-	ns	$-I_{\rm D} = -200 {\rm mA}$

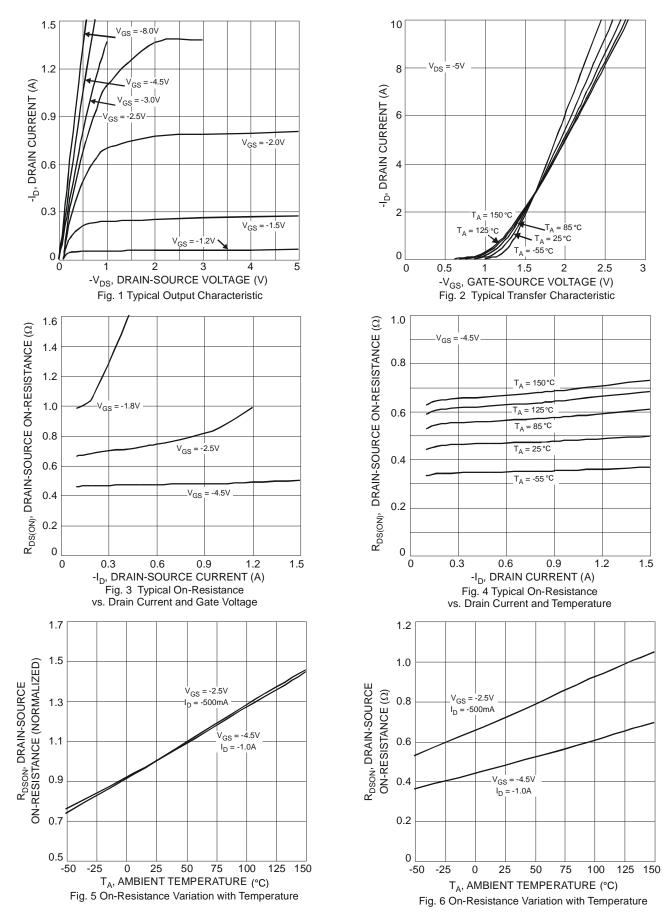
Notes: 6. For a device surface mounted on a minimum recommended pad layout of an FR-4 PCB, in still air conditions; the device is measured when operating in steady-state condition.

7. Same as note 5, except the device is pulsed at duty cycle of 1% for a pulse width of 10µs.

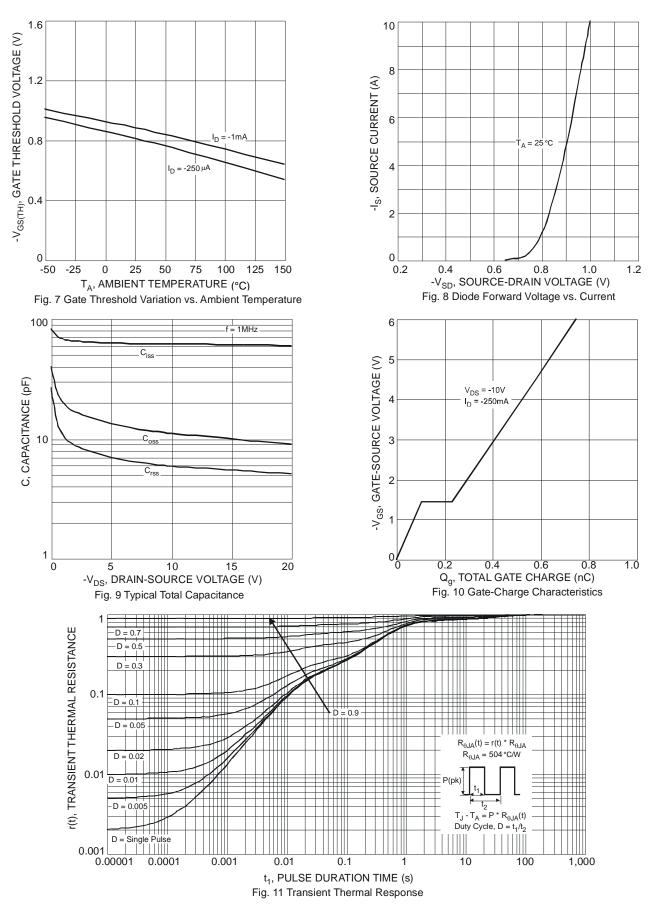
8. Measured under pulsed conditions to minimize self-heating effect. Pulse width ≤ 300µs; duty cycle ≤ 2%.

9. For design aid only, not subject to production testing.







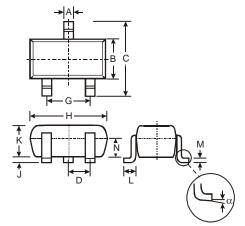




Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT523

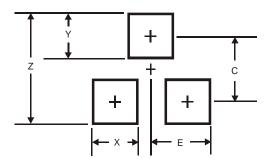


SOT523							
Dim	Min	Max	Тур				
Α	0.15	0.30	0.22				
В	0.75	0.85	0.80				
С	1.45	1.75	1.60				
D			0.50				
G	0.90	1.10	1.00				
н	1.50	1.70	1.60				
J	0.00	0.10	0.05				
Κ	0.60	0.80	0.75				
L	0.10	0.30	0.22				
М	0.10	0.20	0.12				
Ν	0.45	0.65	0.50				
α	0°	8°					
All	All Dimensions in mm						

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT523



Dimensions	Value (in mm)
Z	1.8
Х	0.4
Y	0.51
С	1.3
E	0.7



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